



Crystal Detector Element (CDE) Development Studies

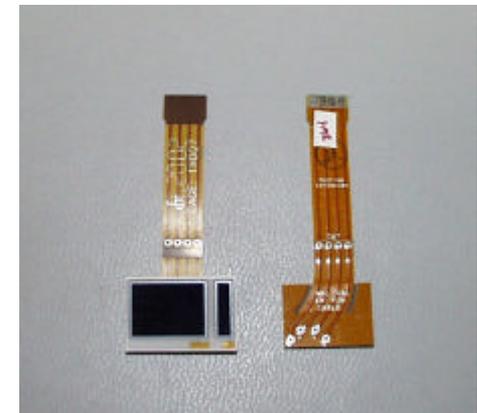
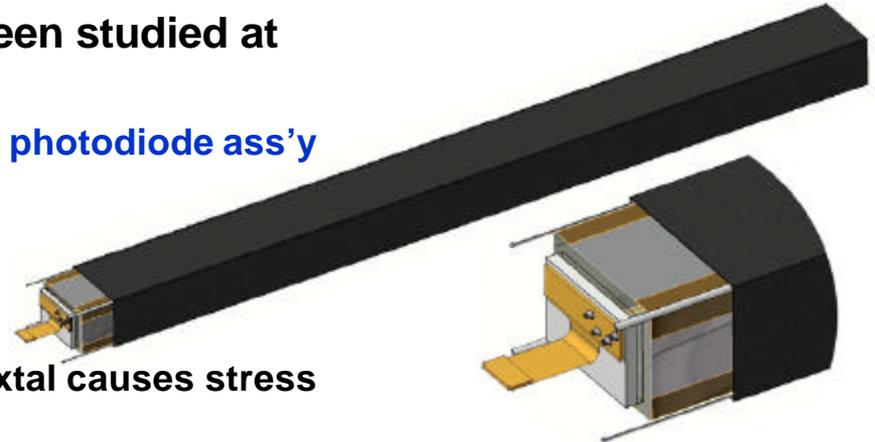
July 2002

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CDE Development

- ❑ Fabrication processes for CDE have been studied at NRL and selected for EM fabrication.
 - CDE = wrapped Csl Crystal bonded with photodiode ass'y (PDA) at each end.
 - Processes defined since PDR
 - Bonding of PDA to Csl xtal
 - CTE mismatch between PDA and xtal causes stress in bond
 - » Hard epoxies fail, silicones (without primer) don't adhere
 - Need soft, flexible bond with strong adhesion
 - **Solution: Silicone elastomer with primer. Bond laid up in mold that defines geometry.**
 - Wrapping of xtal
 - Material is 3M VM2000 non-metallic, specular, reflective film
 - » High light yield, good optical properties
 - » Material is stiff, difficult to fold or wrap
 - **Solution: Mold in mandrel at 120C for 2 hrs at final shape**



Dual PIN photodiode with flex cable = photodiode assembly

Scope of Bonding Studies

□ Assumptions

- The bond shall be made with DC93-500 silicone encapsulant, with DC92-023 primer applied to all bonding surfaces.
- The bond thickness shall be 0.7 ± 0.1 mm.
- The bond material shall not extend past the edges of the diode, lest it interfere with the bumper.
- The crystal surface shall be roughened to improve adhesion.

□ Parameters studied

- Method of bond lay-up
 - Selected one-stage mold with mask to define bond geometry
 - Encapsulant is injected into bounded volume
- Mix ratio of DC93-500 encapsulant
 - **Conclusion: vendor-recommended 10:1 is soft enough after cure**
- Amount and method of DC92-023 primer to be applied
 - **Conclusion: measured volume of primer is spread with spatula**
- Surface treatment of diode and xtal (factory polish or roughened)
 - **Conclusion: diode to remain polished, xtal to be roughened**





Bonding Methods Studied

- ❑ Four bonding methods studied at NRL and Swales
 - “Spacer” method (at NRL).
 - Deliver measured amount of 93-500 between diode and xtal held fixed distance apart.
 - OK, but susceptible to measurement errors. **Rejected.**
 - “Two-stage” method (at NRL).
 - Create pad of 93-500 on diode face, cure for one day, wet surface of 93-500 and apply to xtal.
 - OK, but susceptible to incomplete curing. **Rejected.**
 - “Two-stage” method (at Swales).
 - Similar to NRL version, but uses more 93-500 in 2nd stage and more precise volume.
 - OK, but complex. **Rejected.**
 - “One-stage” method (at Swales).
 - Form bond within break-apart Teflon mold holding diode and xtal.
 - Makes very strong and precise bonds. **Selected.**



Bonding Method Selected

❑ One-stage mold

▪ Principles of method

- Bond is formed within break-apart Teflon mold holding diode and xtal
- Mold precisely defines bond thickness, area, and location on face of xtal
- Mold is sealed against xtal face to prevent leakage of silicone encapsulant
- Encapsulant is injected into bond cavity and allowed to flow until any trapped bubbles are removed

▪ Bonding procedure is written and configured

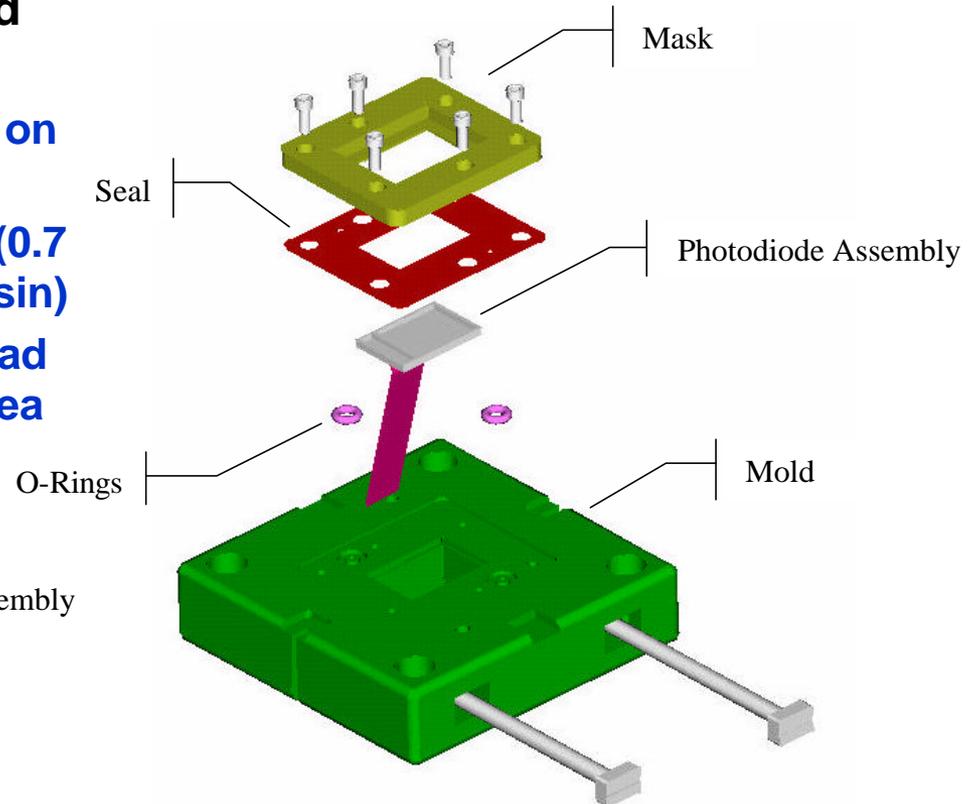
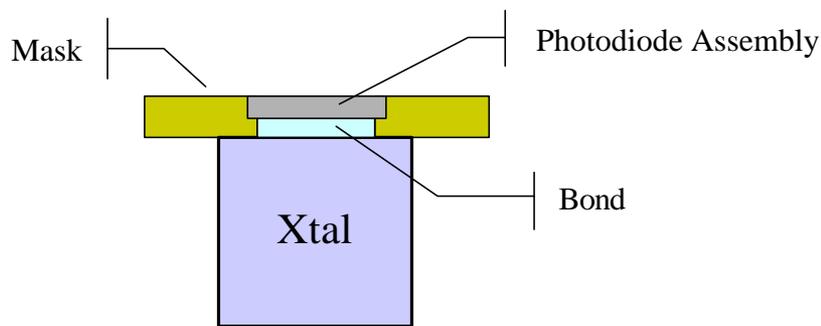
- “Process Specification for the Bonding of the PIN Photodiode Subassembly to the CsI Crystals”, LAT-PS-00385-01



Bonding fixtures

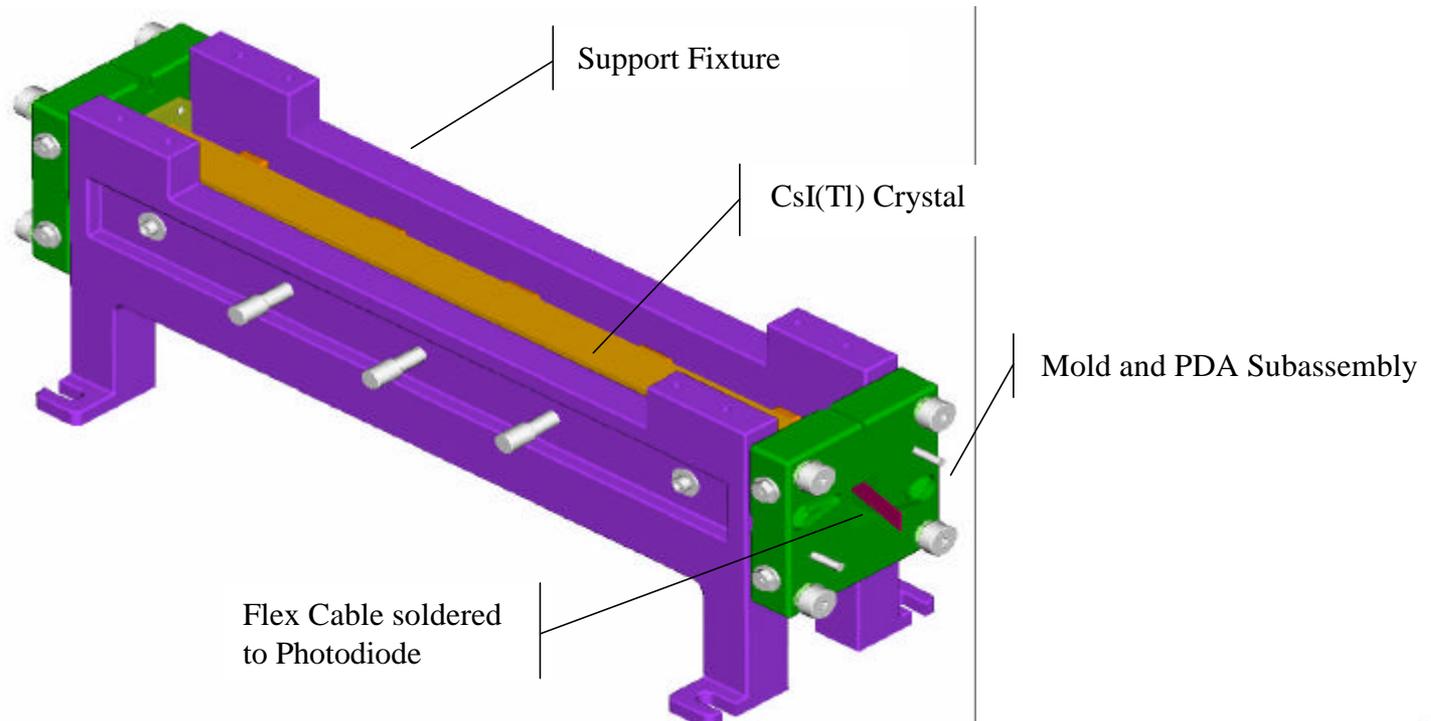
❑ Exploded view of PDA and Mold subassembly

- **Mold:** defines location of bond on xtal (referenced to xtal corner)
- **Mask:** defines bond thickness (0.7 mm) and area (covers epoxy resin)
- **Seal and O-rings:** prevent spread of encapsulant outside bond area



Bonding fixtures

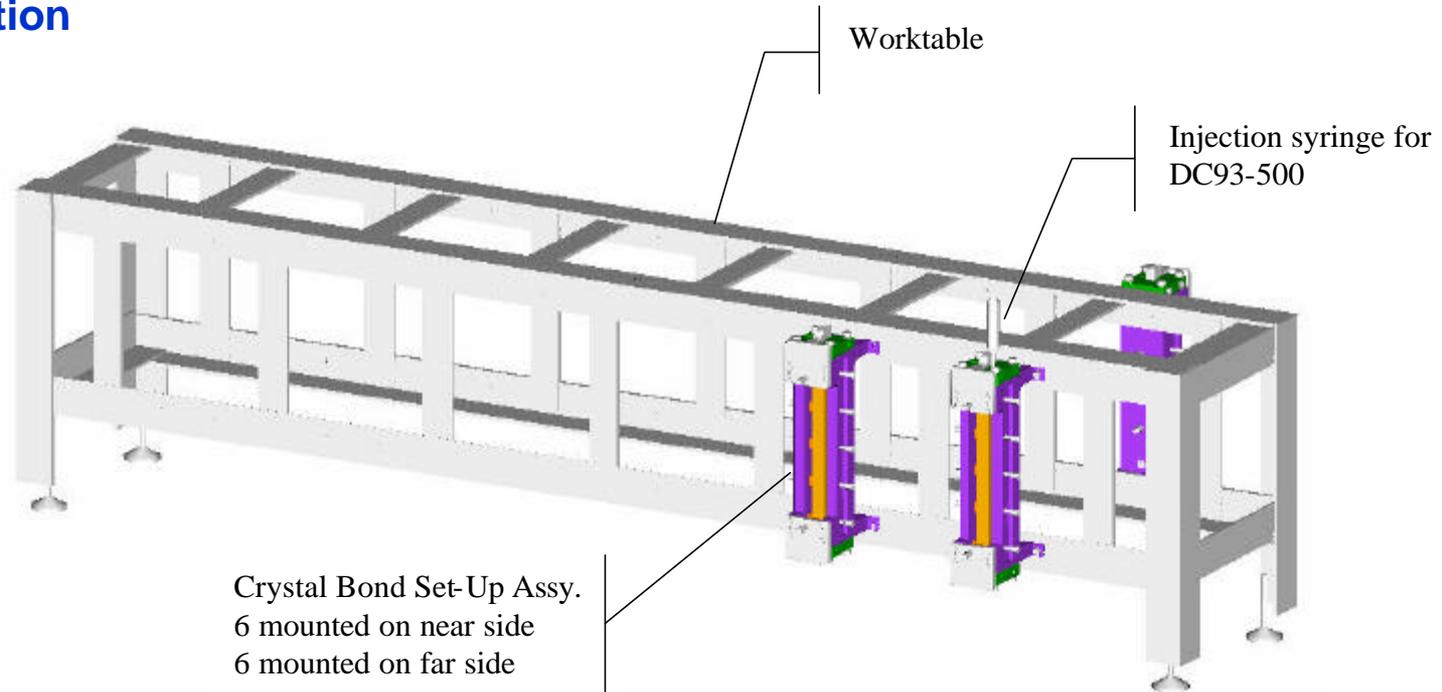
- ❑ **Fixture and molds for single crystal**
 - Independent bonding molds are created for each crystal end
 - Support sleeve prevents distortion of crystal and registers mold to corner of crystal



Bonding fixtures

□ Bonding work station

- 12 bonding stations, six on each side
- Encapsulant is injected with CDE in vertical position



Bond Process

❑ Process at Swales Aerospace

1. Prepare Surfaces

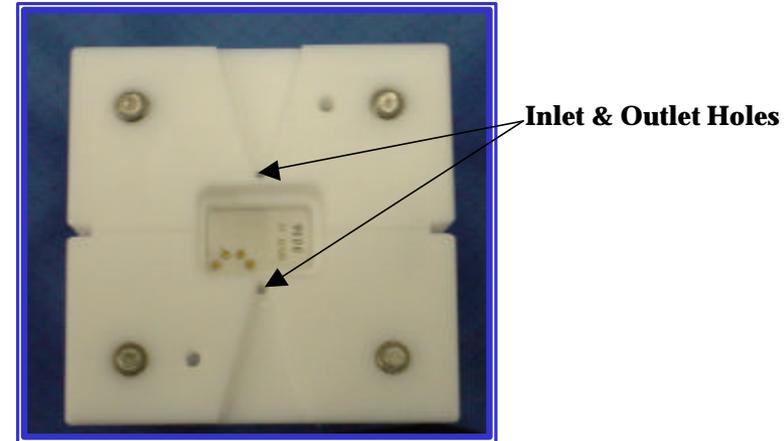
- Clean factory-polished diode bond surface
- Clean roughened crystal surface
- Allow cleaned surfaces to air dry

2. Position Crystal into Fixture and Prime

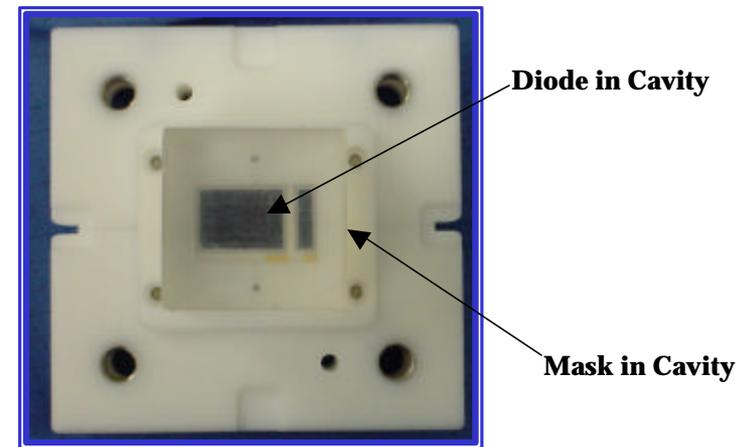
- Position xtal into fixture
- Adjust pads to align xtal into proper position
- Prime xtal surface with DC92-023

3. Position Photodiode into Mold and Prime

- Assemble diode into mold cavity
- Create desired bond area by assembling mask to mold assembly
- Prime diode surface with DC92-023



**Figure 1: Diode in Mold,
Top Side of Mold**



**Figure 2: Diode & Mask in Mold,
Back Side of Mold**

Bond Process (cont.)

4. Join Mold and Xtal fixture

- Assemble fixture (which now contains crystal) to mold assembly
- Preload crystal to mask/diode surface to create a tight seal

5. Apply Adhesive

- Prepare adhesive mixture and de-gas
- Slowly pour mixed/degassed adhesive into syringe
- Inject adhesive into mold inlet hole until the bond cavity is filled

6. After Injection

- Wipe clean adhesive from areas around inlet and outlet hole
- Cure for 24 hours until tack free
- Remove bonded crystal & diode from mold after 24 hours
- Allow bond to finish 7-day cure

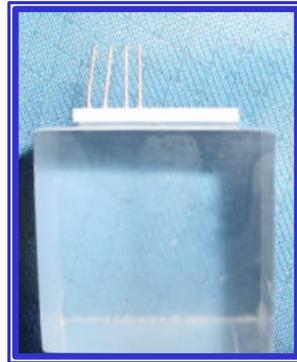


Mechanical Test Sample Bonds

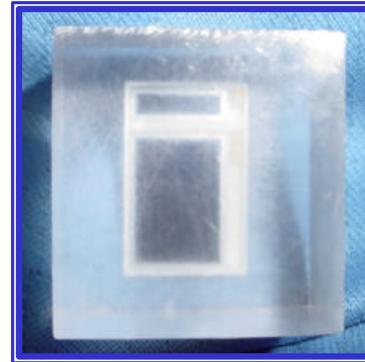
(All Bonds Displayed No Bubbles & Desired Bond Profile (Area & Thickness; Bond Maintained in Ceramic Frame))



**Figure 13: EM Diode on Xtal,
Side View**



**Figure 14: EM Diode on Xtal,
Front View**



**Figure 15: EM Diode on Xtal,
Back View**



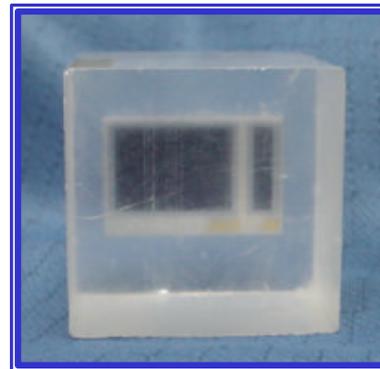
**Figure 16: EM Diode on Xtal,
Side View**



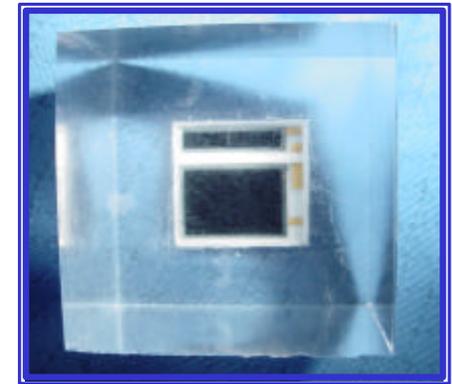
**Figure 16: EM Diode on Xtal,
Side View**



**Figure 17: EM Diode on Xtal,
Front View**



**Figure 18: EM Diode on Xtal,
Back View**



**Figure 19: EM Diode on Plexiglas,
Back View**
Naval Research Lab
Washington DC



Light Yield

- ❑ Light yield tests were performed on sample xtals 3 x 3 x 19 cm
 - Requirement on CDE
 - >6000 e/MeV in large PIN photodiode
 - Tests were performed on sample xtals
 - Xtal size = 3 x 3 x 19 cm
 - EM photodiode
 - Tetratex wrap
 - Samples exposed to radioactive source with known line energy
 - Measured yield (after 50 thermal cycles)
 - 6200 – 7000 e/MeV
 - Expect yield of >7500 e/MeV for EM dimensions with VM2000 wrap





Thermal Cycling

- ❑ Bonds need to be mechanically strong and maintain optical properties
 - To survive handling loads
 - To survive thermal cycling in test, shipping, and storage

- ❑ How do we know a bond has survived?
 - A bond can be mechanically strong and show no visual evidence of separation, at the same time that it has optically failed!
 - Bond process qualification plan must include readout of scintillation light.
 - Visual inspection is inadequate and unacceptable as proof of bond quality.

- ❑ Thermal cycling
 - Full qualification range: -30C to $+50\text{C}$
 - Gradient: 20C per hour (if much steeper, xtals can't keep up)
 - Soak: 1 hour at -30C , 1 hour at $+50\text{C}$
 - Irradiate xtal sample with ^{137}Cs , monitor 662 keV centroid after series of thermal cycles

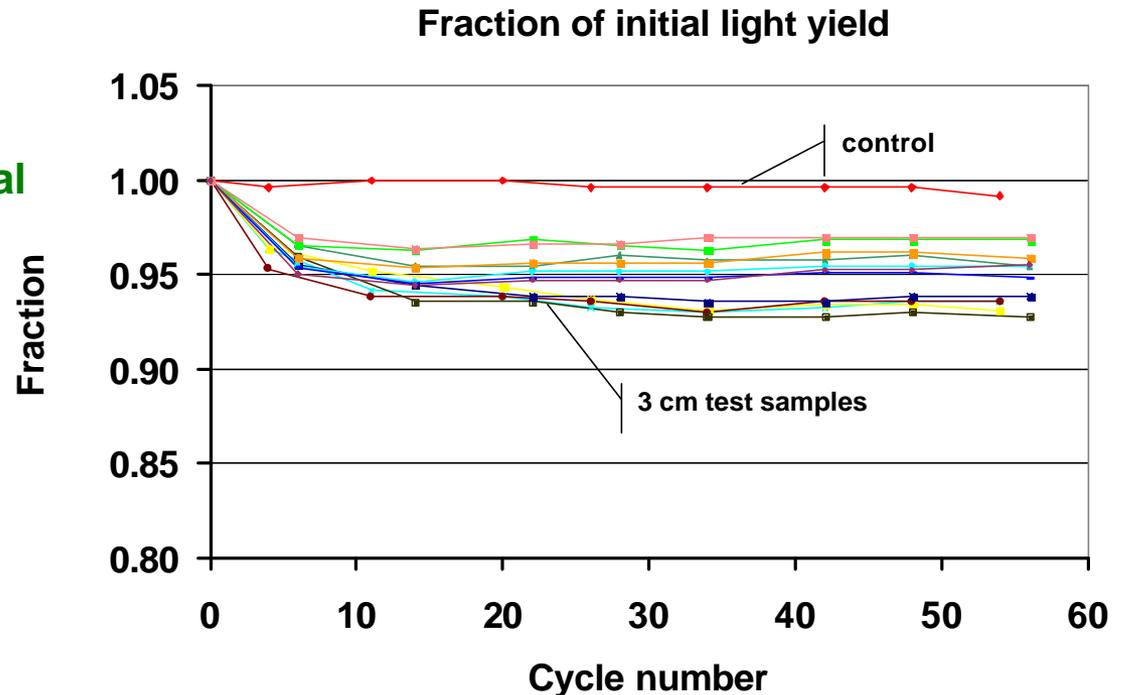




Thermal Cycling

- Optical performance of test samples under thermal cycling
 - Test samples are 3 x 3 x 3 cm cubes with single EM photodiode
 - Test samples typically decline ~5% from their initial light yields and reach plateau
 - Expect this to translate to ~10% decline in CDEs

- Optical properties of bonds survive thermal cycling
- Bonding process creates thermally stable bonds

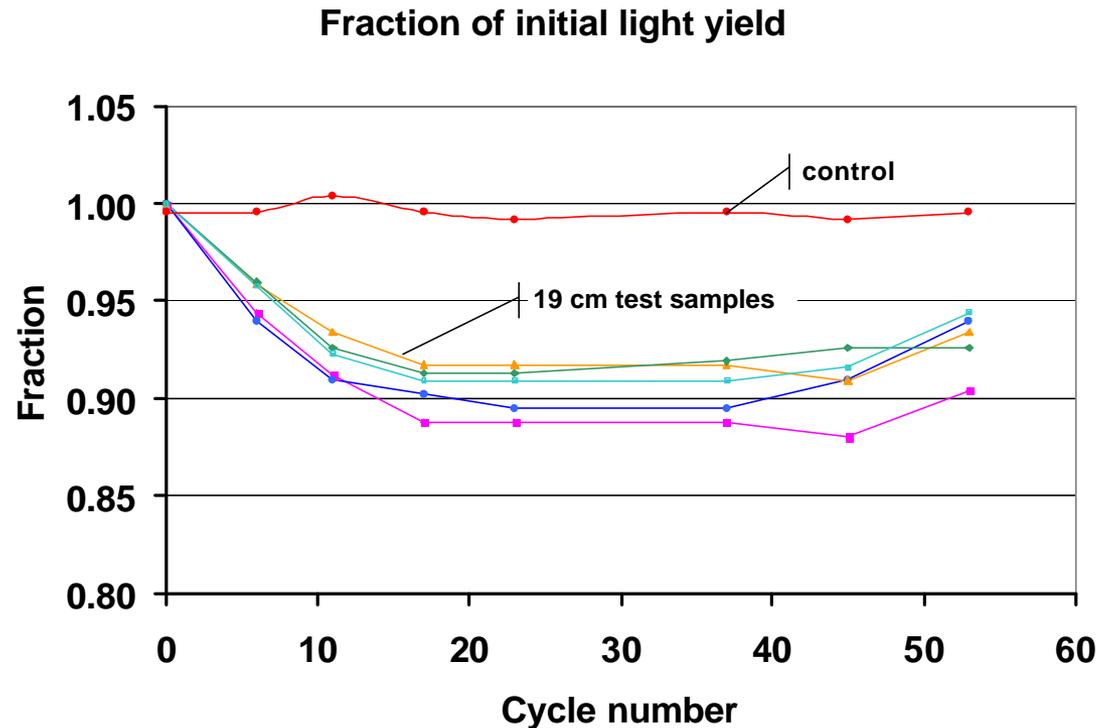


Thermal Cycling

□ Optical performance of longer xtal samples

- Longer xtals samples are 3 x 3 x 19 cm with EM diodes on both ends
- Typically decline ~10% from initial light yield
- Expect same performance from CDEs

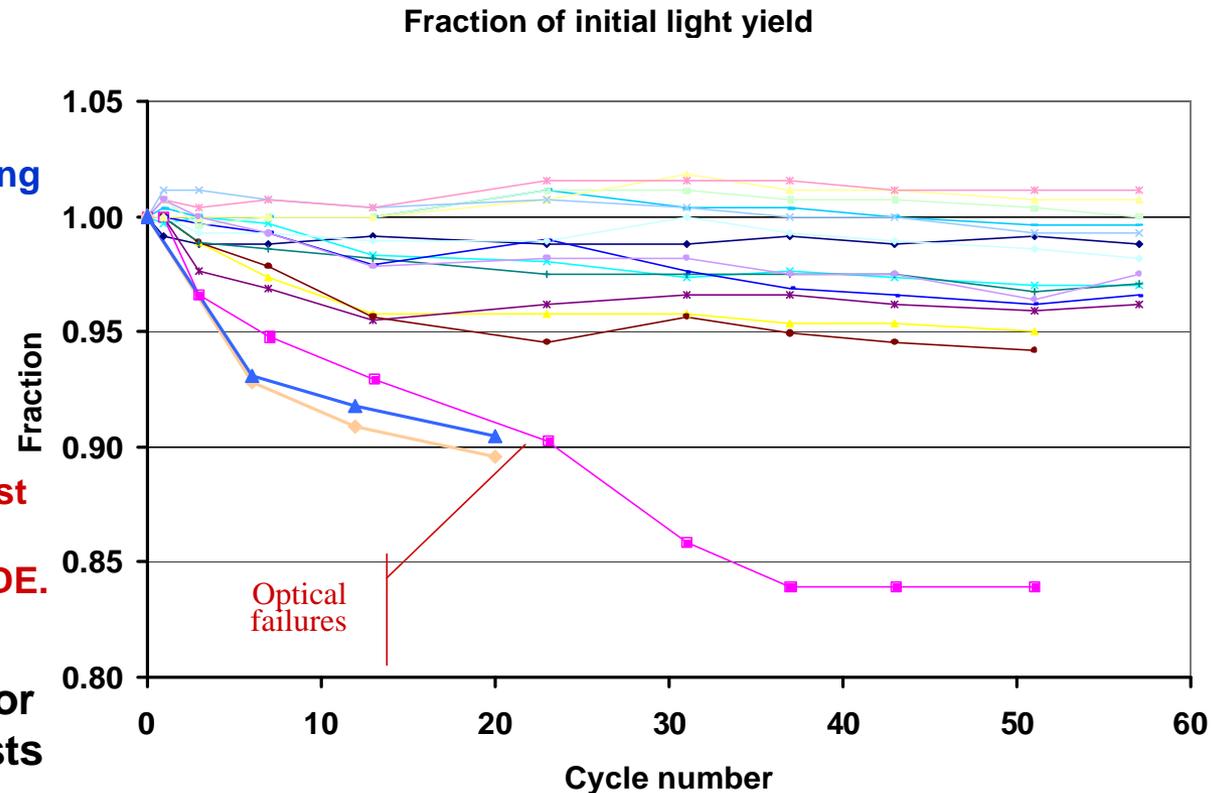
- Again, bonding process creates thermally stable bonds
- Adhesion problem is solved





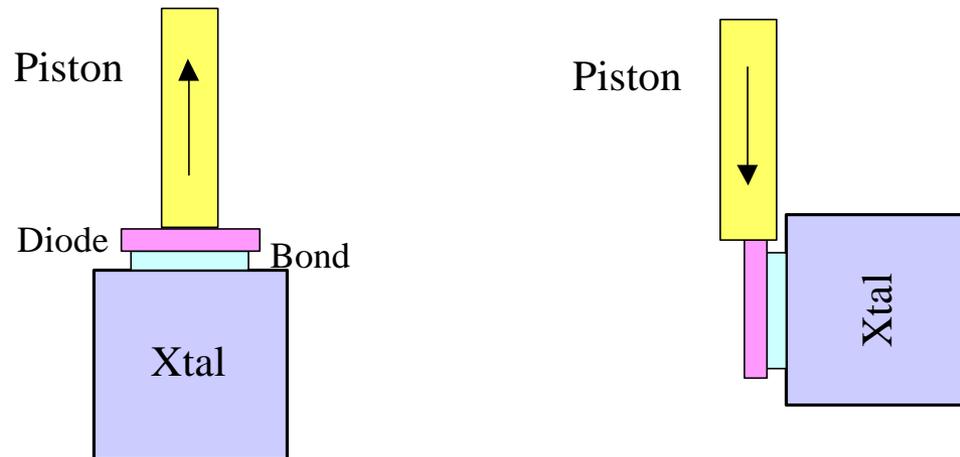
Early Thermal Cycling Tests

- ❑ **Prior to creation of stable bonding process**
- ❑ **16 sample bonds**
 - Created with several methods early in bonding study
 - 13 survive cycling
 - 3 have optical failure
- ❑ **Optical failures**
 - ~15% degradation in test sample is equivalent to ~50% degradation in CDE.
- ❑ **We extracted samples for mechanical strength tests after optical failure...**



Mechanical Strength Tests

- ❑ Two types of destructive tests have been performed at NRL
 - Tensile strength
 - CETIM requirement: 10 N (2.2 lbf)
 - Shear strength
 - CETIM requirement: 0.12 N/mm² (8 lbf = 35 N for EM diode)
 - >35 samples tested
- ❑ Samples are pulled or sheared to failure in Dynamic Load Test Stand

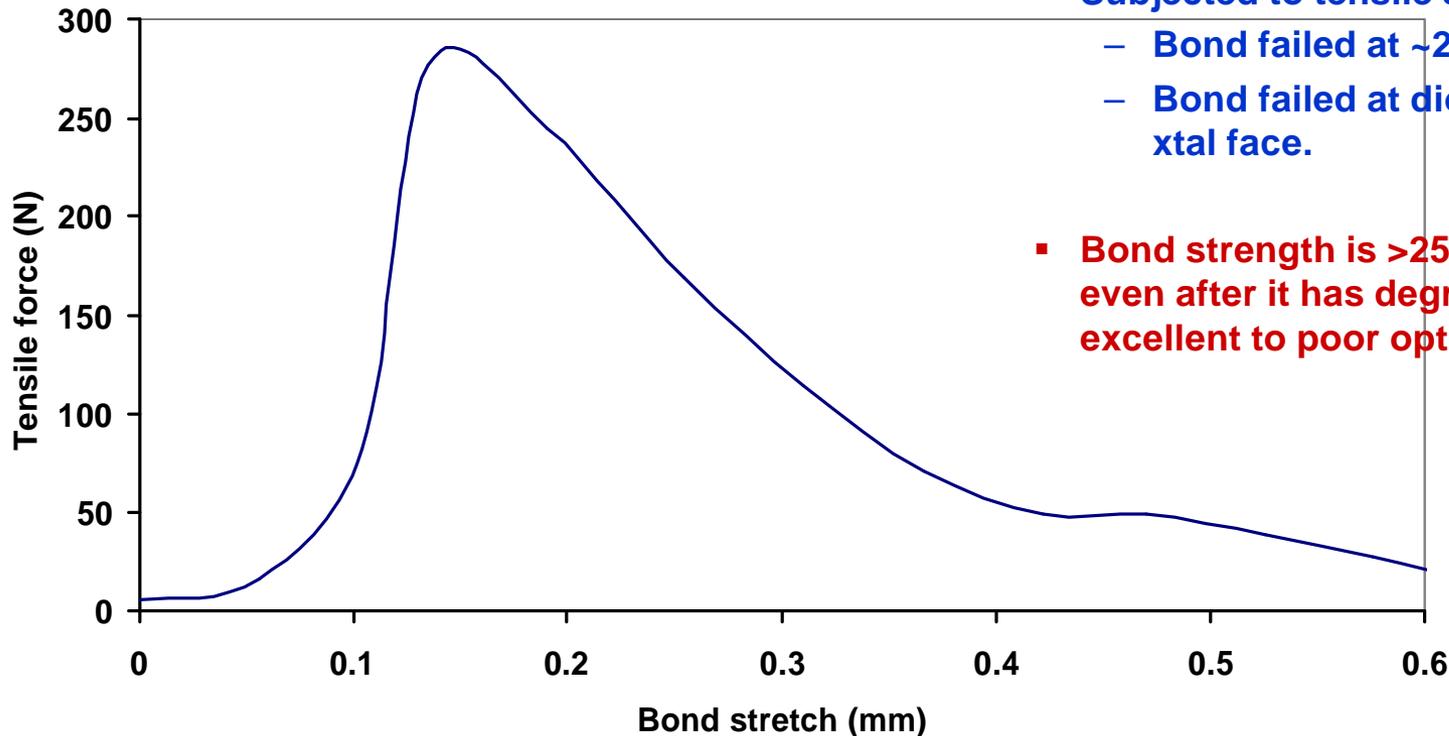


Tensile Strength Test

☐ Swales one-stage bond

- After optical failure in thermal cycling
- Visual inspection showed no evidence for air gaps, delamination, separation, peeling, etc.
- Subjected to tensile strength test
 - Bond failed at ~280 N.
 - Bond failed at diode face, not at xtal face.
- **Bond strength is >25x requirement, even after it has degraded from excellent to poor optical contact.**

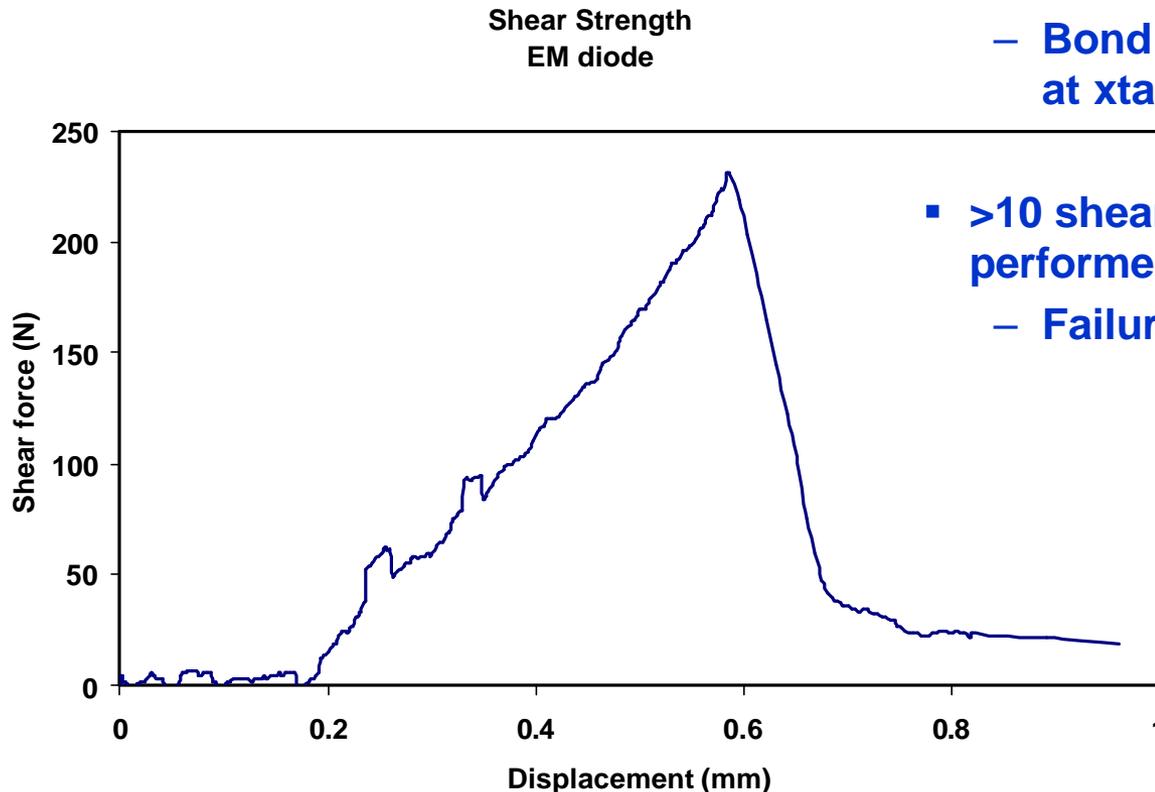
One-stage bond
Swales crystal sample 02-005



Shear Strength Test

□ Swales one-stage bond

- Subjected to shear strength test
 - Bond failed at ~240 N.
 - Bond failed at diode face, not at xtal face.



- >10 shear tests have been performed
 - Failure occurs typ. at >300 N

Crystal Wrapping (LAT-PS-00795-01)

❑ VM2000 specular film

- Gives 20-30% more light than standard diffusive white wraps (e.g. Tyvek, Tetratex)
- Stable, rigid material will not wet xtal surface as Teflon-based wraps can (e.g. Tetratex)
- Non-metallic, so no grounding issues
- Rigid, so awkward to wrap
 - Tried rolling, folding, spiral winding...
 - All created loose, awkward wraps

❑ Solution: Hot molding

- Method
 - Form VM2000 around aluminum mandrel in xtal form (with chamfers)
 - Heat at 120 C for 2 hrs
- Material takes and holds sharp corners of mandrel
- Trivial to wrap around xtal, simple Kapton tape tacking
- No loss in light yield or mechanical stability from hot molding





Wrapping Studies & Conclusions

- ❑ **VM2000 Max. Molding Temperature as Specified by 3M is 125°C for 5 hrs.**
 - At this temperature or any other temperature below, material properties (mechanical, physical and optical) are NOT compromised as long as material is mechanically supported.

- ❑ **Temperatures Studied For VM2000 Molding**
 - 50°C, 75°C, 100°C, 120°C, 150°C

- ❑ **Duration of Time for Molding Process at all Temperatures**
 - 1 hour, 2 hrs., 3 hrs.

- ❑ **Conclusions:**
 - the higher and the longer the temperature, the more defined the wrapping form
 - 150°C is too high for any duration of time tested
 - 100°C and 120°C for 3 hours and 2 hours respectively is ideal
 - Molding VM2000 in oven allows wrap to be preformed days/weeks before actual wrapping process on real crystal has to be performed.



Wrapping Mold Set-Up



Wrap & Chamfer Close-Up

